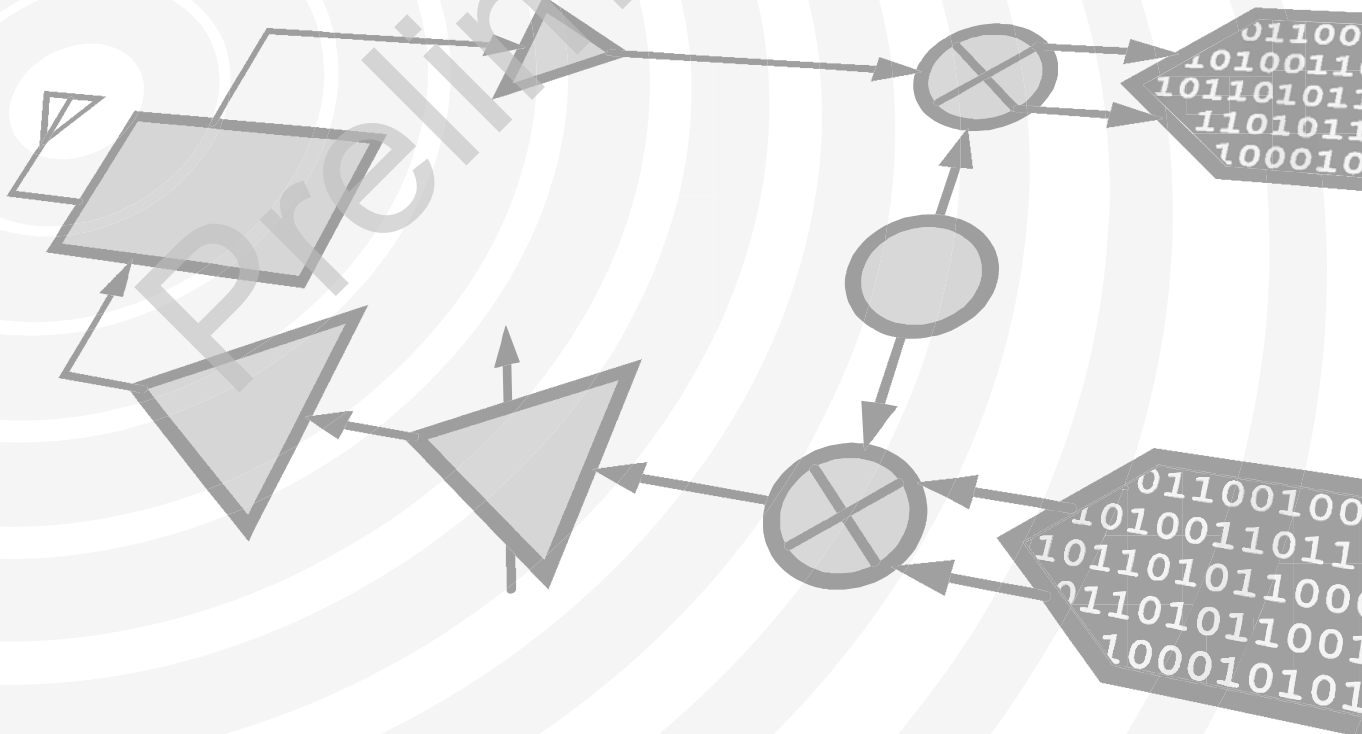


Analog Devices Welcomes Hittite Microwave Corporation



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Preliminary

GaAs MMIC SPDT NON-REFLECTIVE SWITCH, DC - 20 GHz

Typical Applications

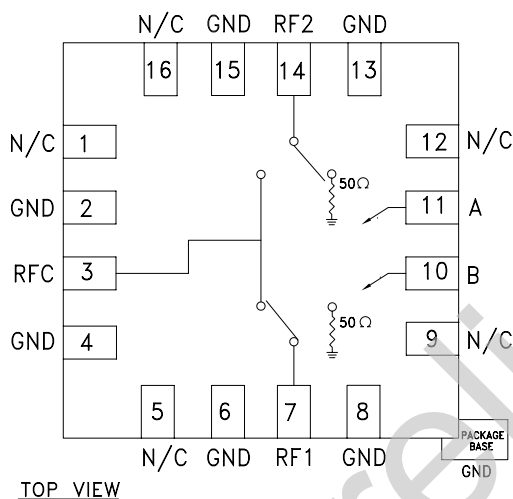
The HMC547ALP3 & HMC547ALP3E is ideal for:

- Basestation Infrastructure
- Fiber Optics & Broadband Telecom
- Microwave Radio & VSAT
- Military Radios, Radar, & ECM
- Test Instrumentation

Features

- High Isolation: >50 dB up to 5 GHz
>45 dB up to 15 GHz
- Low Insertion Loss: 1.6 dB @ 10 GHz
2 dB @ 20 GHz
- Fast Switching
- Non-Reflective Design
- QFN SMT Package, 9 mm²

Functional Diagram



General Description

The HMC547ALP3 & HMC547ALP3E are general purpose broadband high isolation non-reflective GaAs MESFET SPDT switches in low cost leadless QFN surface mount plastic packages. Covering DC to 20 GHz, the switch offers high isolation and low insertion loss. The switch features >50 dB isolation up to 5 GHz and >45 dB isolation up to 15 GHz. The switch operates using complementary negative control voltage logic lines of -5/0V and requires no bias supply. The HMC547ALP3 & HMC547ALP3E are packaged in leadless QFN 3x3 mm surface mount packages.

Electrical Specifications, $T_A = +25^\circ\text{C}$, With 0/-5V Control, 50 Ohm System

Parameter	Frequency	Min.	Typ.	Max.	Units
Insertion Loss	DC - 6.0 GHz		1.5	1.9	dB
	DC - 10.0 GHz		1.6	2.0	dB
	DC - 15.0 GHz		1.8	2.2	dB
	DC - 20.0 GHz		2.0	2.5	dB
Isolation	DC - 6.0 GHz	45	50		dB
	DC - 15.0 GHz	40	45		dB
	DC - 20.0 GHz	33	38		dB
Return Loss "On State"	DC - 20.0 GHz		17		dB
Return Loss RF1, RF2 "Off State"	DC - 6.0 GHz		25		dB
	DC - 15.0 GHz		17		dB
	DC - 20.0 GHz		13		dB
Input Power for 1 dB Compression	0.5 - 20.0 GHz	20	23		dBm
Input Third Order Intercept (Two-Tone Input Power= +7 dBm Each Tone)	0.5 - 10.0 GHz		48		dBm
	0.5 - 20.0 GHz		45		dBm
Switching Characteristics	DC - 20 GHz				
			3		ns
			6		ns

**GaAs MMIC SPDT NON-REFLECTIVE
SWITCH, DC - 20 GHz**
Absolute Maximum Ratings

RF Input Power (Vctl = -5V)	+30 dBm
Control Voltage Range (A & B)	+0.5V to -7.5 V
Hot Switch Power Level (Vctl = -5V)	+23 dBm
Channel Temperature	150 °C
Continuous Pdiss (T=85°C) (derate 4 mW/°C about 85°C)	0.26 W
Thermal Resistance (Insertion Loss Path)	420 °C/W
Thermal Resistance (Terminated Path)	250 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 1A

Control Voltages

State	Bias Condition
Low	0 to -0.5V @ 10 uA Max.
High	-5V @ 3 uA Typ. to -7V @ 10 uA Typ. (± 0.5 V)

Truth Table

Control Input		Signal Path State	
A	B	RFC to RF1	RFC to RF2
High	Low	On	Off
Low	High	Off	On



**ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS**

Outline Drawing
